

0.25 Ω Low-Voltage Dual SPDT Analog Switch

DESCRIPTION

The DG3535, DG3536 is a sub 1 Ω (0.25 Ω at 2.7 V) dual SPDT analog switches designed for low voltage applications.

The DG3535, DG3536 has on-resistance matching (less than 0.05 Ω at 2.7 V) and flatness (less than 0.2 Ω at 2.7 V) that are guaranteed over the entire voltage range. Additionally, low logic thresholds makes the DG3535, DG3536 an ideal interface to low voltage DSP control signals.

The DG3535, DG3536 has fast switching speed with break-before-make guaranteed. In the On condition, all switching elements conduct equally in both directions. Off-isolation and crosstalk is - 69 dB at 100 kHz.

The DG3535, DG3536 is built on Vishay Siliconix's high-density low voltage CMOS process. An epitaxial layer is built in to prevent latchup. The DG3535, DG3536 contains the additional benefit of 2000 V ESD protection.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switching products manufactured with tin/silver/copper (SnAgCu) device terminations, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- Low voltage operation
- Low on-resistance - R_{ON} : 0.25 Ω at 2.7 V
- - 69 dB OIRR at 2.7 V, 100 kHz
- MICRO FOOT® package
- ESD protection > 2000 V

BENEFITS

- Reduced power consumption
- High accuracy
- Reduce board space
- 1.6 V logic compatible
- High bandwidth

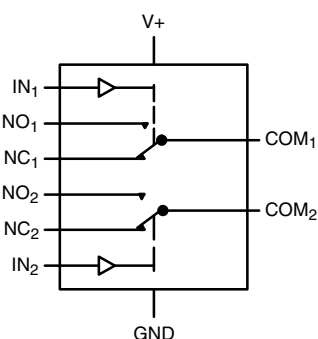
APPLICATIONS

- Cellular phones
- Speaker headset switching
- Audio and video signal routing
- PCMCIA cards
- Battery operated systems
- Relay replacement


RoHS
COMPLIANT

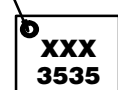
FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

DG3535, DG3536
MICRO FOOT 10-Bump



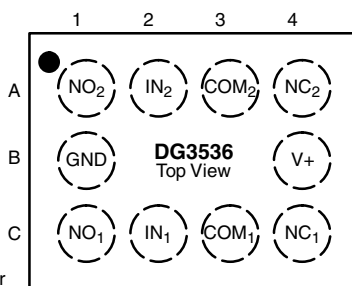
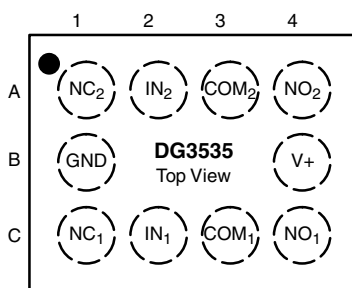
Device Marking

A1 Locator



3535 = Example Base Part Number

xxx = Data/Lot Traceability Code



TRUTH TABLE

Logic	NC1 and NC2	NO1 and NO2
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION

Temp. Range	Package	Part Number
- 40 °C to 85 °C	MICRO FOOT: 10 Bump (4 x 3, 0.5 mm Pitch, 238 μ m Bump Height)	DG3535DB-T5-E1 DG3535DB-T1-E1 DG3536DB-T5-E1

ABSOLUTE MAXIMUM RATINGS

Parameter	Limit	Unit
Reference V+ to GND	- 0.3 to + 6	V
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3 V)	
Continuous Current (NO, NC, COM)	± 300	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)	± 500	
Storage Temperature	(D Suffix)	°C
Package Solder Reflow Conditions ^b	IR/Convection	
ESD per Method 3015.7	> 2	kV
Power Dissipation (Packages) ^c	MICRO FOOT: 10 Bump (4 x 3 mm) ^d	mW

Notes:

a Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b Refer to IPC/JEDEC (J-STD-020B)

c All bumps welded or soldered to PC board.

d Derate 5.7 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 3.0 V)

Parameter	Symbol	Test Conditions Otherwise Unless Specified $V_+ = 3\text{ V}, \pm 10\%, V_{IN} = 0.5\text{ V}$ or 1.4 V^e	Temp. ^a	Limits - 40 to 85 °C			Unit
				Min. ^b	Typ. ^c	Max. ^b	
Analog Switch							
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V_+	V
On-Resistance ^d	R_{ON}	$V_+ = 2.7\text{ V}, V_{COM} = 0.6/1.5\text{ V}$ $I_{NO}, I_{NC} = 100\text{ mA}$	Room Full		0.25	0.4 0.5	Ω
R_{ON} Flatness ^d	R_{ON} Flatness		Room			0.15	
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		Room			0.05	
Switch Off Leakage Current	$I_{NO(off)}$ $I_{NC(off)}$	$V_+ = 3.3\text{ V},$ $V_{NO}, V_{NC} = 0.3\text{ V}/3\text{ V}, V_{COM} = 3\text{ V}/0.3\text{ V}$	Room Full	- 2 - 20		2 20	nA
	$I_{COM(off)}$		Room Full	- 2 - 20		2 20	
Channel-On Leakage Current	$I_{COM(on)}$	$V_+ = 3.3\text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3\text{ V}/3\text{ V}$	Room Full	- 2 - 20		2 20	
Digital Control							
Input High Voltage ^d	V_{INH}		Full	1.4			V
Input Low Voltage	V_{INL}		Full			0.5	
Input Capacitance	C_{in}		Full		10		pF
Input Current	I_{INL} or I_{INH}	$V_{IN} = 0$ or V_+	Full	1		1	μA



SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10 %,VIN = 0.5 V or 1.4 V ^e	Temp. ^a	Limits - 40 °C to 85 °C			Unit
				Min. ^b	Typ. ^c	Max. ^b	
Dynamic Characteristics							
Turn-On Time	tON	VNO or VNC = 2.0 V, RL = 50 Ω, CL = 35 pF	Room Full		52	82 90	ns
Turn-Off Time	tOFF		Room Full		43	73 78	
Break-Before-Make Time	td		Room	1	6		
Charge Injection ^d	QINJ	CL = 1 nF, VGEN = 1.5 V, RGEN = 0 Ω	Full		21		pC
Off-Isolation ^d	OIRR	RL = 50 Ω, CL = 5 pF, f = 100 kHz	Room		- 69		dB
Crosstalk ^d	XTALK		Room		- 69		
NO, NC Off Capacitance ^d	CNO(off)	VIN = 0 or V+, f = 1 MHz	Room		145		pF
	CNC(off)		Room		145		
Channel-On Capacitance ^d	CNO(on)		Room		406		
	CNC(on)		Room		406		
Power Supply							
Power Supply Current	I+	VIN = 0 or V+	Room Full		0.001	1.0 1.0	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

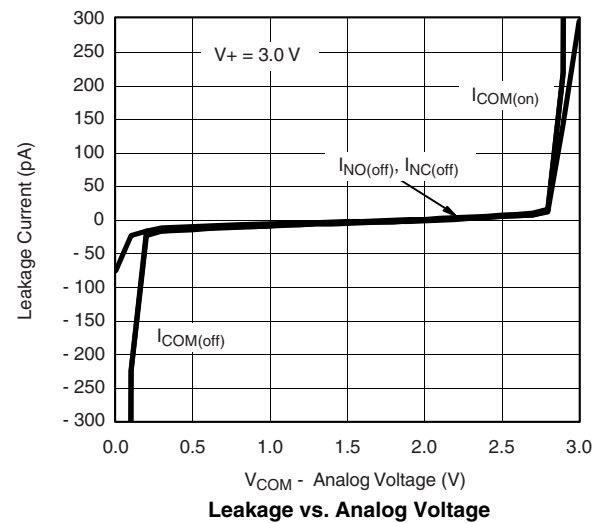
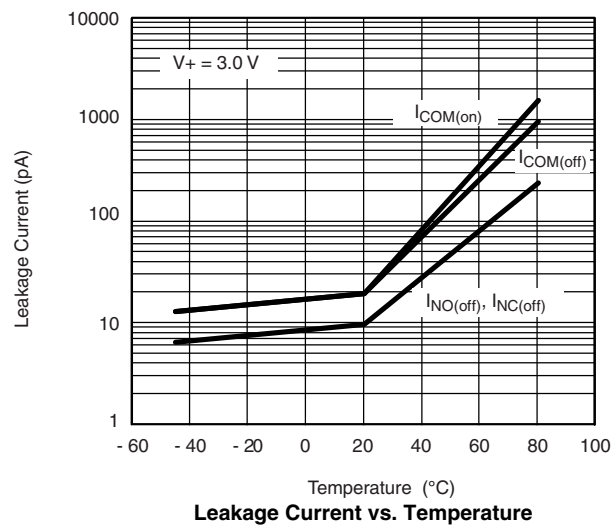
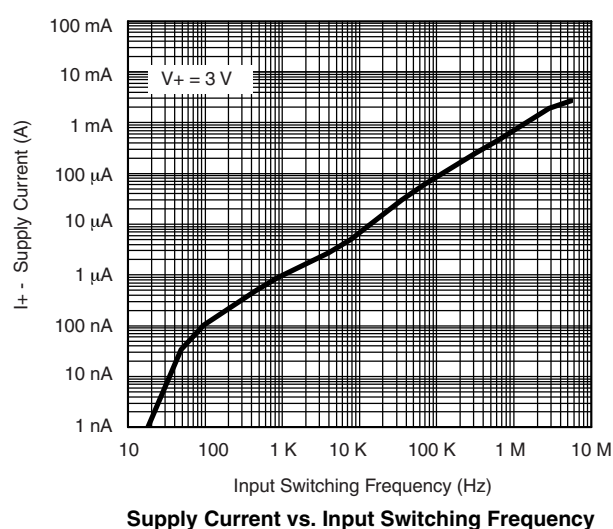
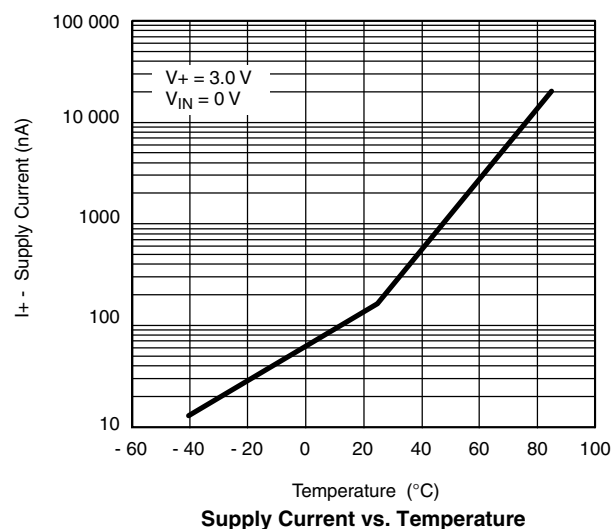
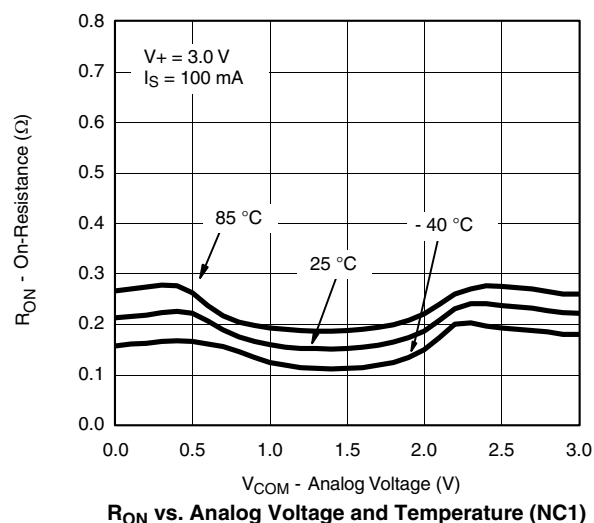
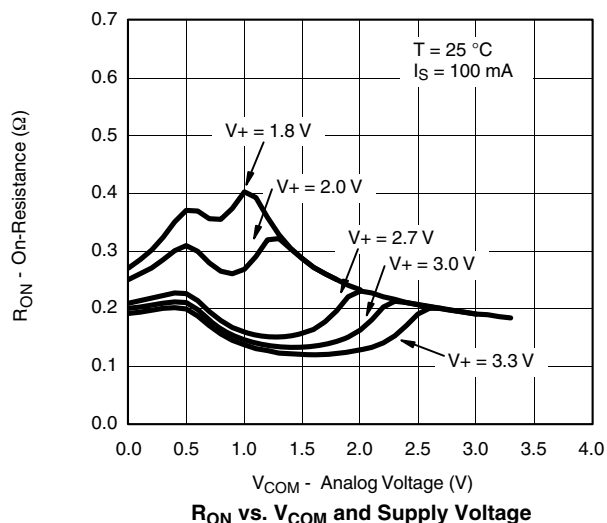
b. Typical values are for design aid only, not guaranteed nor subject to production testing.

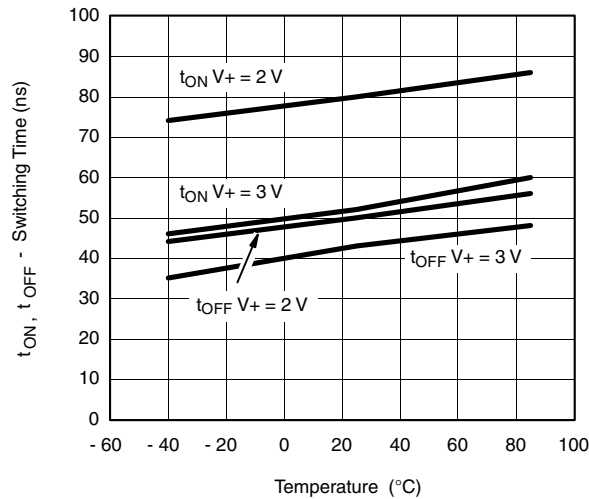
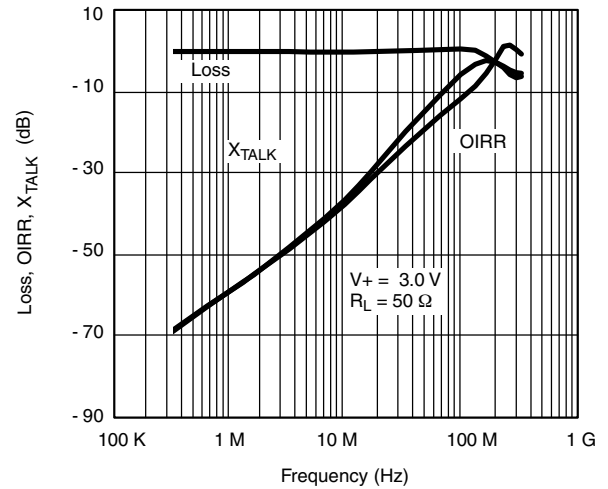
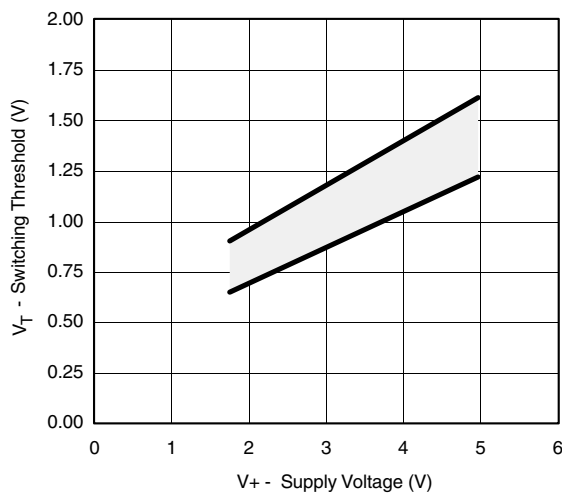
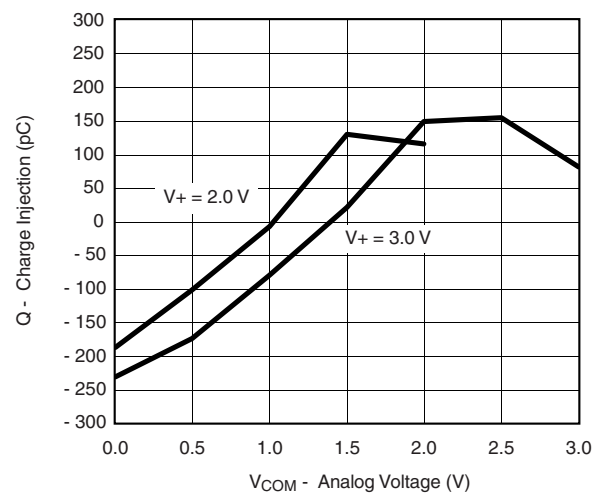
c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Switching Time vs. Temperature

Insertion Loss, Off-Isolation Crosstalk vs. Frequency

Switching Threshold vs. Supply Voltage

Charge Injection vs. Analog Voltage

TEST CIRCUITS

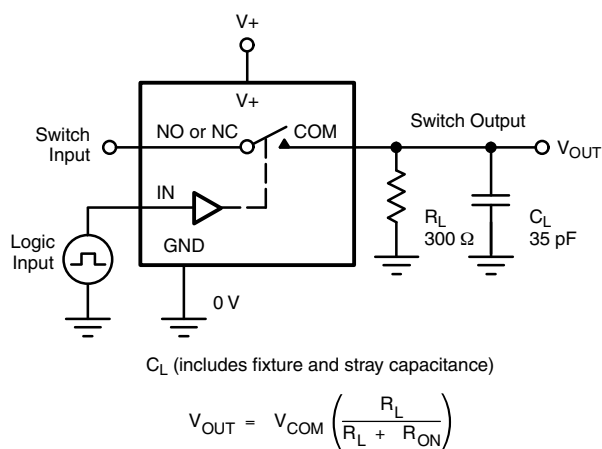


Figure 1. Switching Time

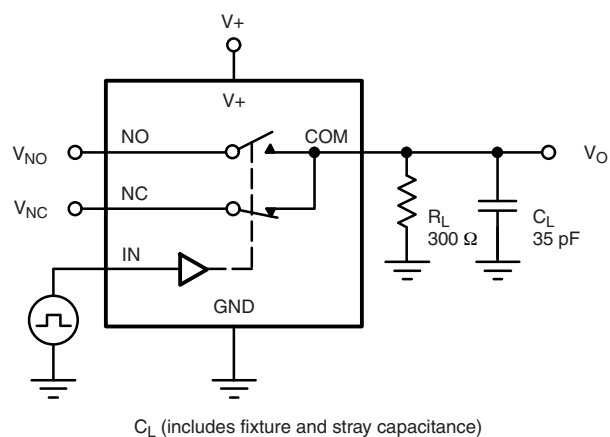


Figure 2. Break-Before-Make Interval

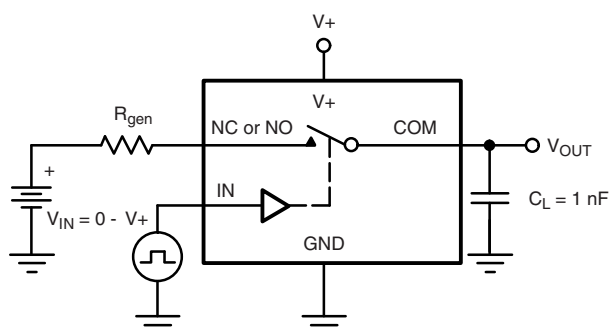
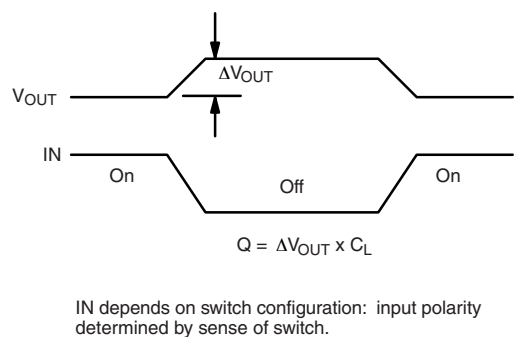
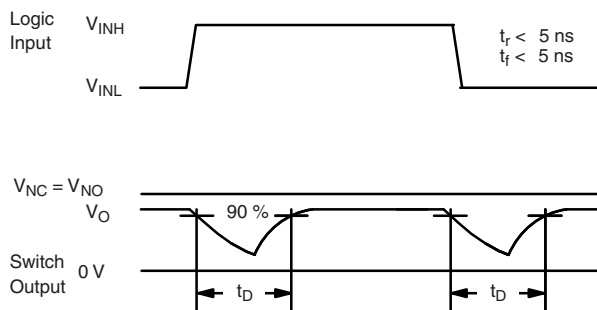
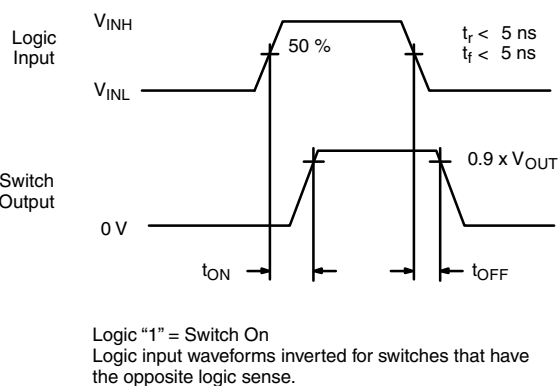
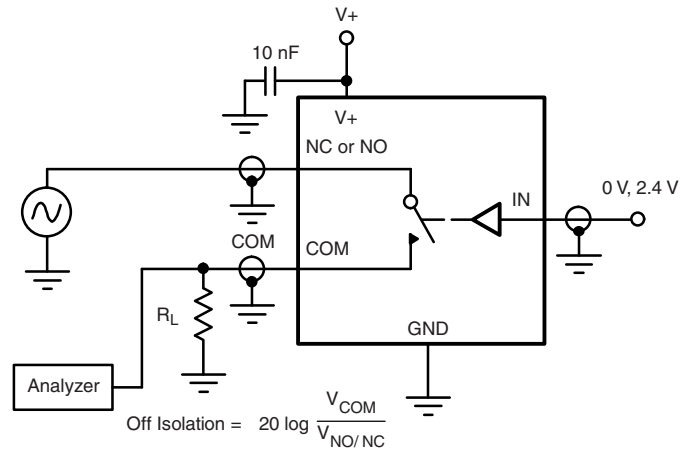
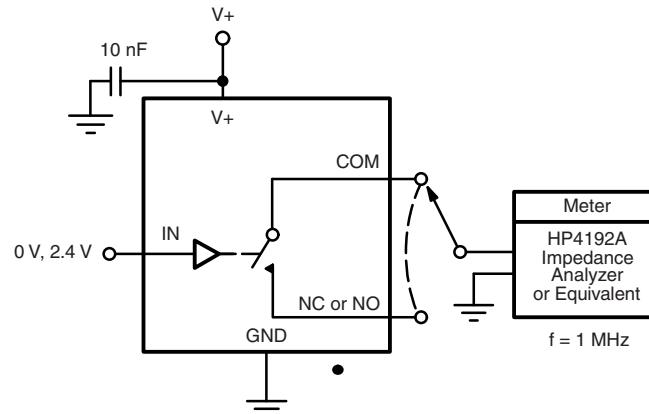


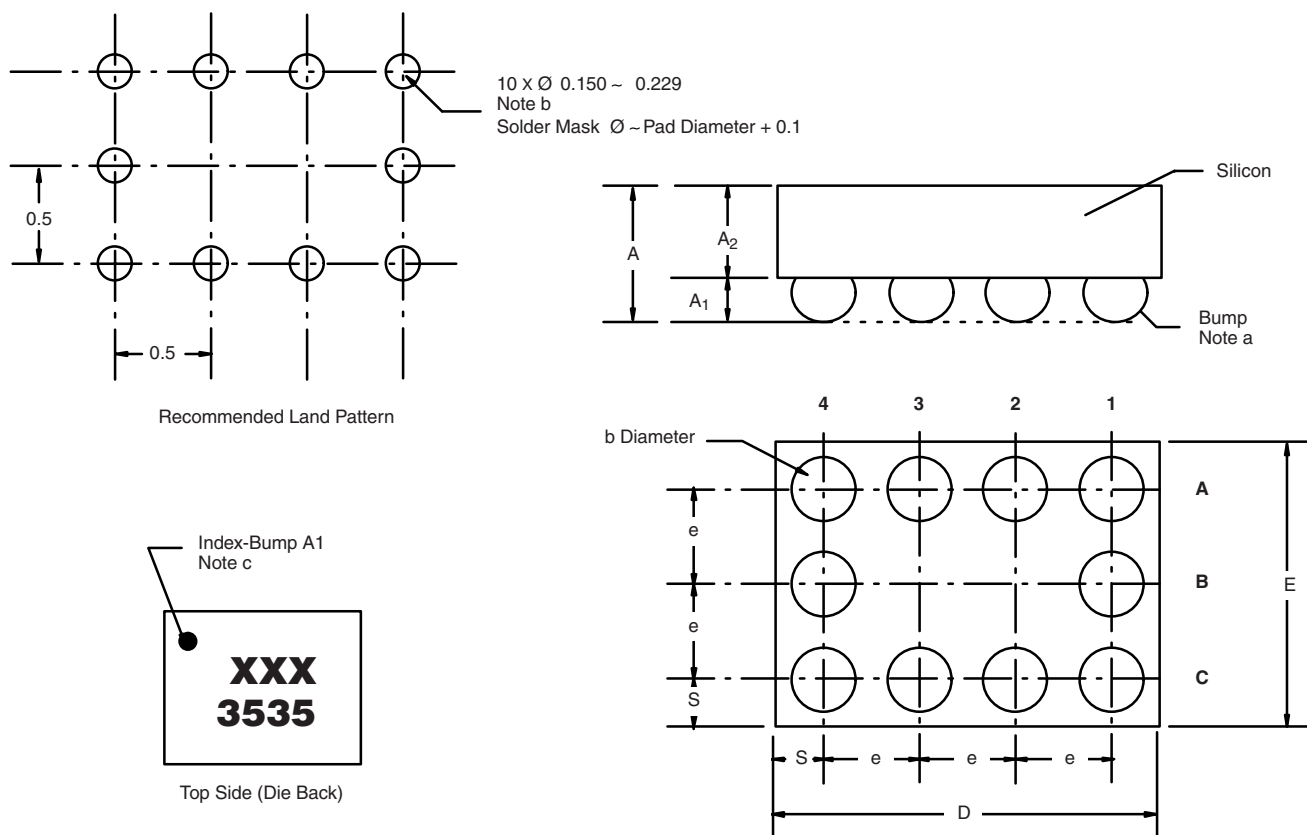
Figure 3. Charge Injection




Figure 4. Off-Isolation

Figure 5. Channel Off/On Capacitance

PACKAGE OUTLINE

MICRO FOOT: 10 BUMP (4 x 3, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

- a. Bump is Lead Free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

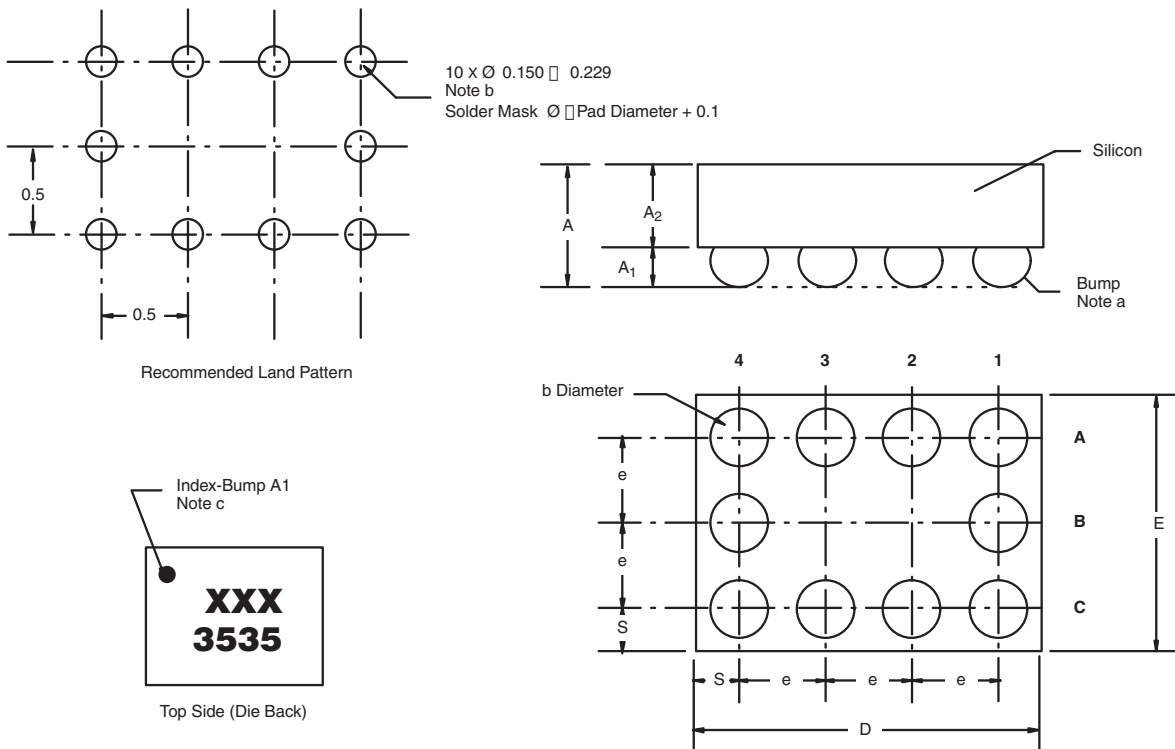
Dim.	Millimeters ^a		Inches	
	Min.	Max.	Min.	Max.
A	0.688	0.753	0.0271	0.0296
A ₁	0.218	0.258	0.0086	0.0102
A ₂	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.980	2.020	0.0780	0.0795
E	1.480	1.520	0.0583	0.0598
e	0.5 BASIC		0.0197 BASIC	
S	0.230	0.270	0.0091	0.0106

Notes:

- a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72961.

MICRO FOOT: 10-BUMP (4 mm x 3 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes

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ECN: S11-1065-Rev. A, 13-Jun-11
DWG: 6001



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